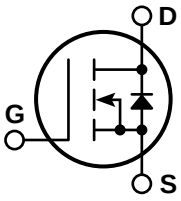

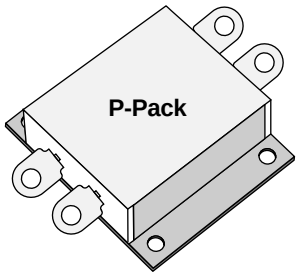

ADVANCED POWER TECHNOLOGY®

APL1001P 1000V 18.0A 0.60Ω

POWER MOS IV® HERMETIC PACKAGE

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APL1001P	UNIT
V_{DSS}	Drain-Source Voltage	1000	Volts
I_D	Continuous Drain Current @ T_C = 25°C	18	Amps
I_{DM}, I_{LM}	Pulsed Drain Current ① and Inductive Current Clamped	72	
V_{GS}	Gate-Source Voltage	±30	Volts
P_D	Total Power Dissipation @ T_C = 25°C	520	Watts
	Linear Derating Factor	4.16	W/°C
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250 µA)	1000			Volts
$I_{D(ON)}$	On State Drain Current ②(V_{DS} > $I_{D(ON)}$ x $R_{DS(ON)}$ Max, V_{GS} = 8V)	18			Amps
$R_{DS(ON)}$	Drain-Source On-State Resistance ②(V_{GS} = 10V, 0.5 I_D [Cont.])			0.60	Ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = V_{DSS}, V_{GS} = 0V)			25	µA
	Zero Gate Voltage Drain Current (V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125°C)			250	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±30V, V_{DS} = 0V)			±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 2.5mA)	2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\Theta JC}$	Junction to Case			0.24	°C/W
$R_{\Theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planar Heat Sink Surface.)		0.06		

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - http://www.advancedpower.com

USA 405 S.W. Columbia Street Bend, Oregon 97702-1035 Phone: (541) 382-8028 FAX: (541) 388-0364

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050-5899 Rev - 8-2001

DYNAMIC CHARACTERISTICS

APL1001P

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		6000	7200	pF
C_{oss}	Output Capacitance			775	1080	
C_{rss}	Reverse Transfer Capacitance			285	430	
t_d(on)	Turn-on Delay Time	V_{GS} = 15V V_{DD} = 0.5 V_{DSS} I_D = I_D [Cont.] @ 25°C R_G = 0.6Ω		14	28	ns
t_r	Rise Time			14	28	
t_d(off)	Turn-off Delay Time			60	92	
t_f	Fall Time			14	20	

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	V_{DS} = 400 V, I_{DS} = 0.813A, t = 20 sec., T_C = 60°C	325			Watts

①Repetitive Rating: Pulse width limited by maximum junction temperature. See Transient Thermal Impedance Curve. (Fig.1)

②Pulse Test: Pulse width < 380 µS, Duty Cycle < 2%

③See MIL-STD-750 Method 3471

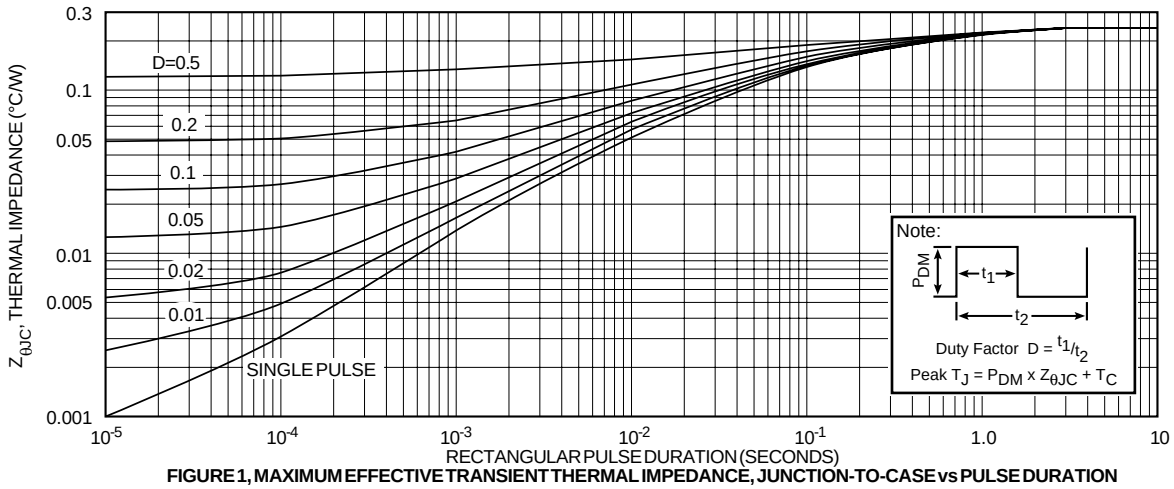


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

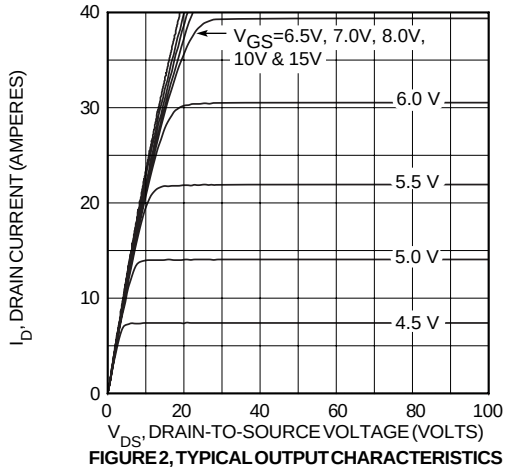


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

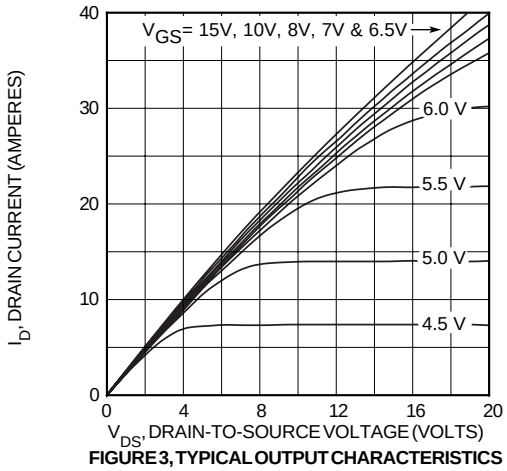


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

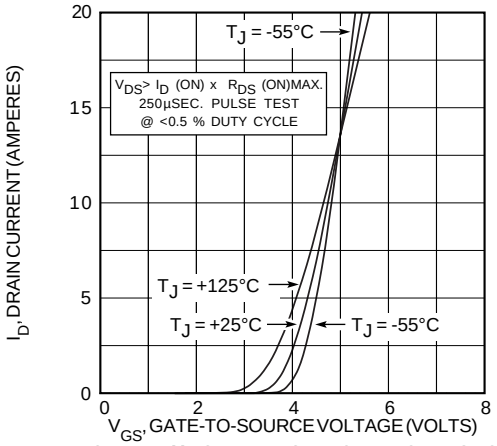


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

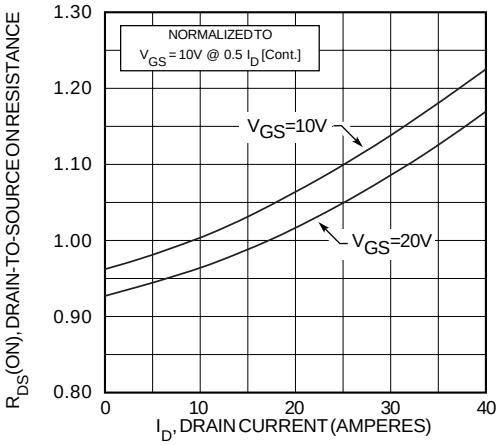


FIGURE 5, R_{DS}(ON) vs DRAIN CURRENT

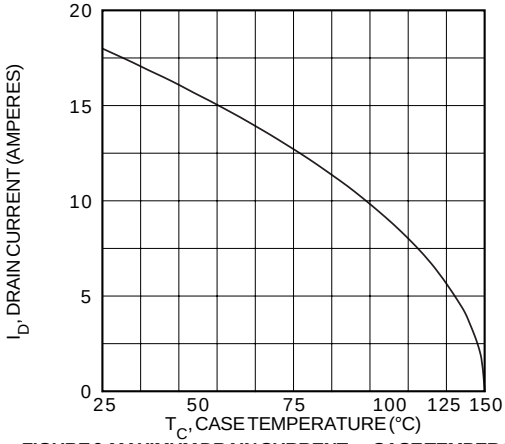


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

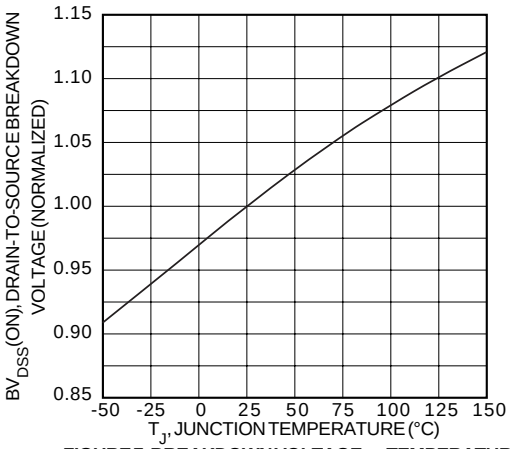


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

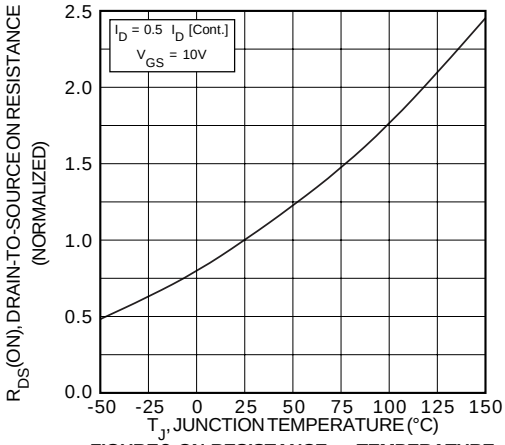


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

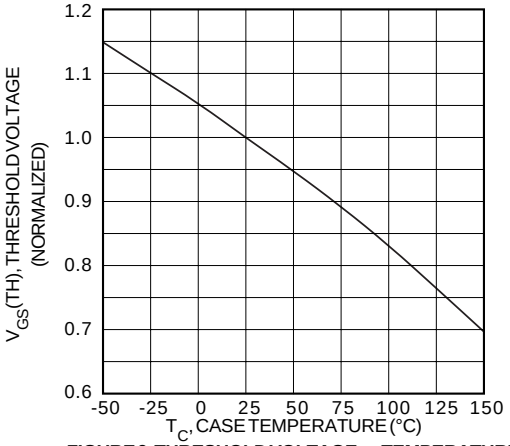


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

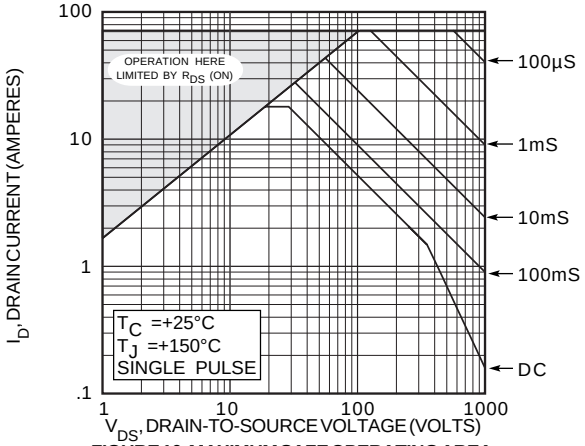


FIGURE 10, MAXIMUM SAFE OPERATING AREA

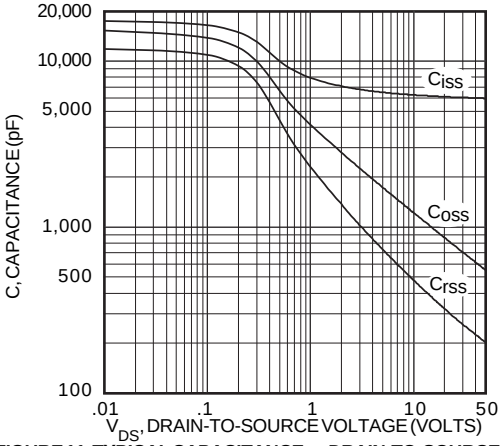
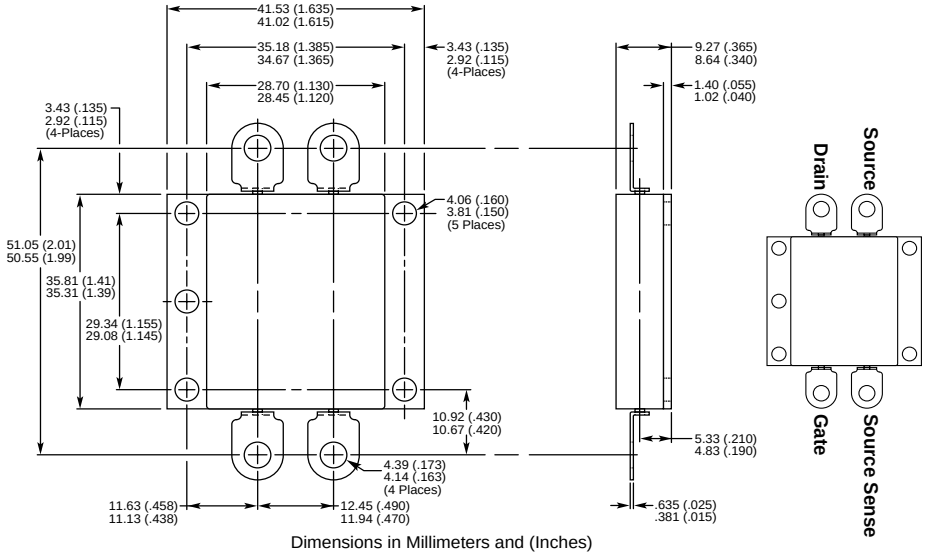


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

P-Pack Package Outline



Dimensions in Millimeters and (Inches)

APT's devices are covered by one or more of the following U.S.patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058